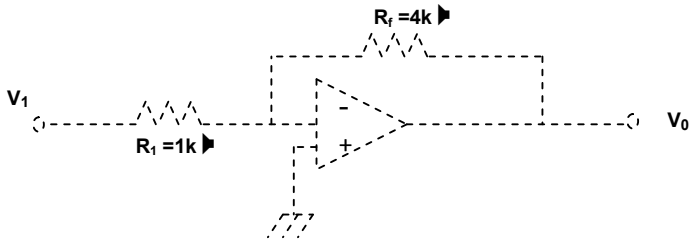
ELECTRONICS & TELECOMMUNICATION ENGINEERING

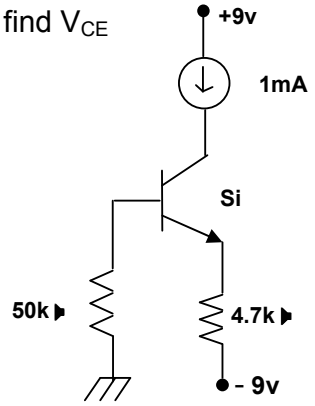
1.



Given the bandwidth of the circuit above is 100MHz. For what value of R_f, the bandwidth will become 25MHz.

(A) 2kΩ (B) 1kΩ (C) 16kΩ (D)None of these

2. For the transistor shown below, β_{DC} = 50, find V_{CE}



(A) 3.13 V

(B) 0.2V

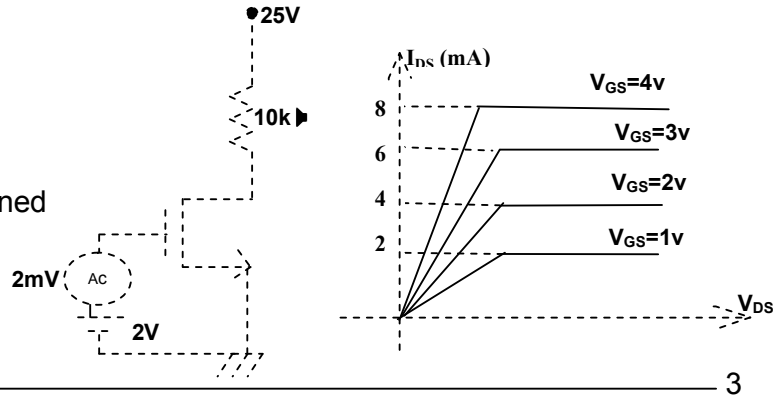
(C) 18V

(D) None of these

3. In a forward biased Ge diode, a current of 26mA is flowing, If the voltage equivalent of temperature is 0.026 v and carrier life time is 20 μ sec, what will be the value of diffusion capacitance

(A) 10 μ F (B) 15 μ F (C) 20 μ F (D) 25 μ F

4. What will be the voltage gain of the following circuit



(A) -20

(B) -10

(C) Cannot be determined

(D) None of these

SPACE FOR ROUGH WORK